

U.S. Application No. 10/051,267

Attorney Docket No. 09792909-5359

IN THE CLAIMS:

Claim 1. (Currently Amended) A bottom-gate thin-film transistor comprising:
a gate electrode, a gate insulating film, an active layer, and a protective
insulating film deposited in that order on a substrate; and

~~various~~ a plurality of layers formed over said protective film with at least one
electrode extending therethrough that is operatively and electrically connected to one of
said active layer, an LDD region ~~or~~ and a source-drain region;

wherein[[,]] the protective insulating film has a thickness of 100 nm or less, and
the protective insulating film is formed on any one of the active layer, [[an]] LDD region,
and [[a]] source-drain region, and

wherein there is no etched mask structure within the thin film transistor structure.

Claim 2. (Original) A bottom-gate thin-film transistor according to Claim 1,
wherein the active layer comprises a polysilicon film.

Claim 3. (Original) A bottom-gate thin-film transistor according to either Claim 1
or 2, wherein the protective insulating film has a thickness of 5 to 50 nm.

Claims 4-9. (Canceled)

Claim 10. (Withdrawn)

Claim 11. (Canceled)

Claim 12. (Withdrawn)

Claim 13. (Canceled)